

Description

The VST15N130 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

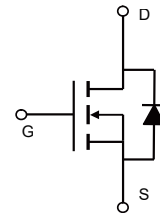
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 150V, I_D = 70A$
 $R_{DS(ON)} = 13.5m\Omega$ (typical) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating



DFN5x6



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST15N130	VST15N130-D56	DFN5x6	-	-	-

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	70	A
Drain Current-Continuous($T_C = 100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	49	A
Pulsed Drain Current	I_{DM}	280	A
Maximum Power Dissipation	P_D	160	W
Derating factor		1.28	W/°C
Single pulse avalanche energy (Note 1)	E_{AS}	583	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.78	°C/W
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	150	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=150V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=35A$	-	13.5	15	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=35A$	-	58	-	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=75V, V_{GS}=0V,$ $F=1.0MHz$	-	2000	-	PF
Output Capacitance	C_{oss}		-	280	-	PF
Reverse Transfer Capacitance	C_{rss}		-	16	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=75V, I_D=35A$ $V_{GS}=10V, R_G=3\Omega$	-	12.5	-	nS
Turn-on Rise Time	t_r		-	3.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	14	-	nS
Turn-Off Fall Time	t_f		-	3.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=75V, I_D=35A,$ $V_{GS}=10V$	-	35	-	nC
Gate-Source Charge	Q_{gs}		-	11.8	-	nC
Gate-Drain Charge	Q_{gd}		-	9.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=35A$	-	-	1.2	V
Diode Forward Current	I_S		-	-	70	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}C, I_F = 35A$ $di/dt = 100A/\mu s$	-	47	-	nS
Reverse Recovery Charge	Q_{rr}		-	65	-	nC

Notes:

1. E_{AS} condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink k, assuming a maximum junction temperature of $T_J(MAX)=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

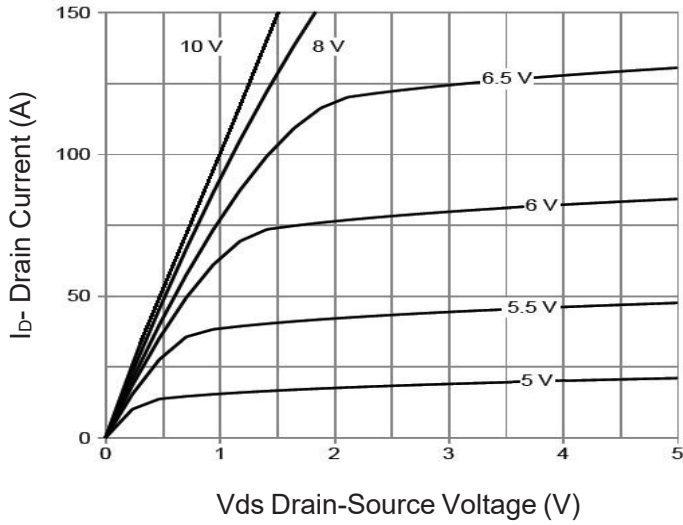


Figure 1 Output Characteristics

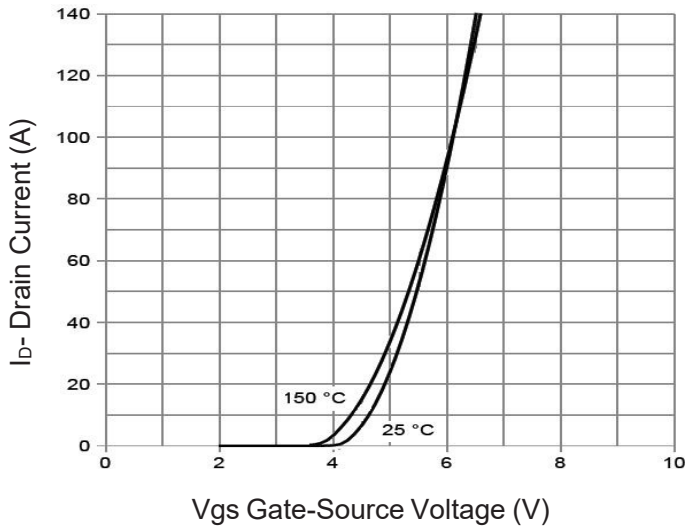


Figure 2 Transfer Characteristics

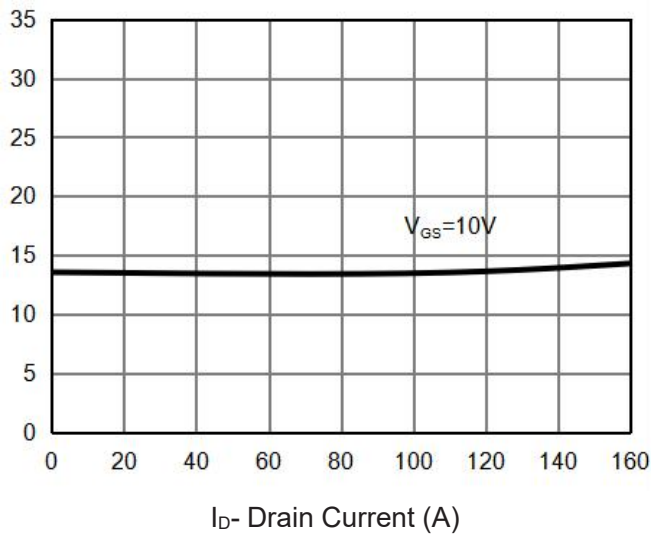


Figure 3 Rdson- Drain Current

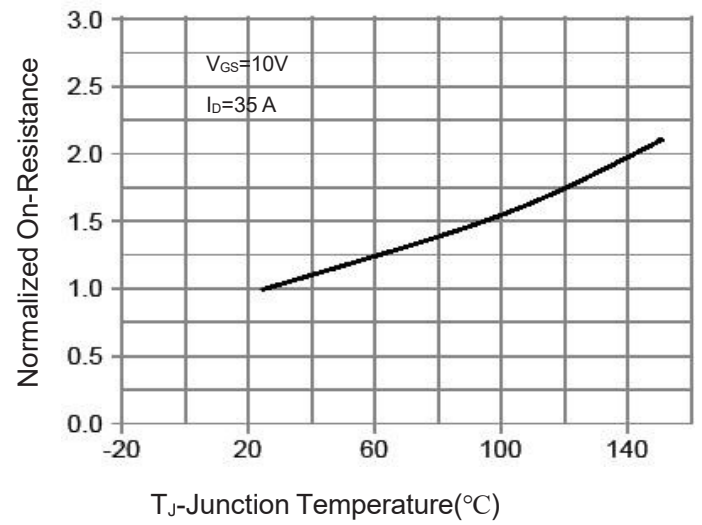


Figure 4 Rdson-Junction Temperature

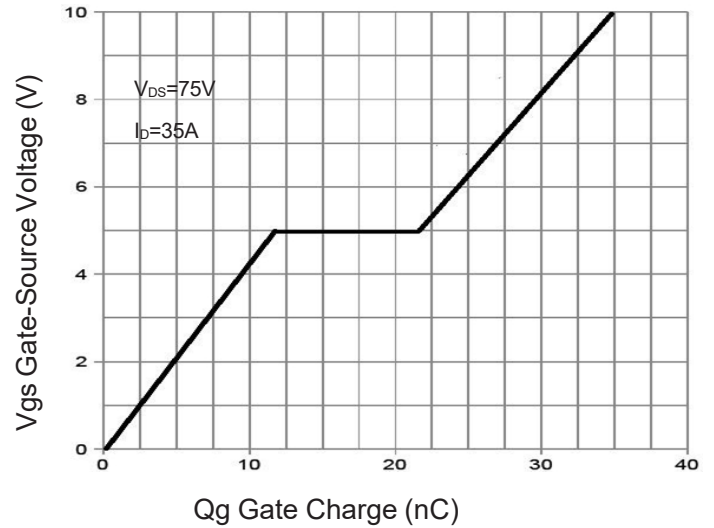


Figure 5 Gate Charge

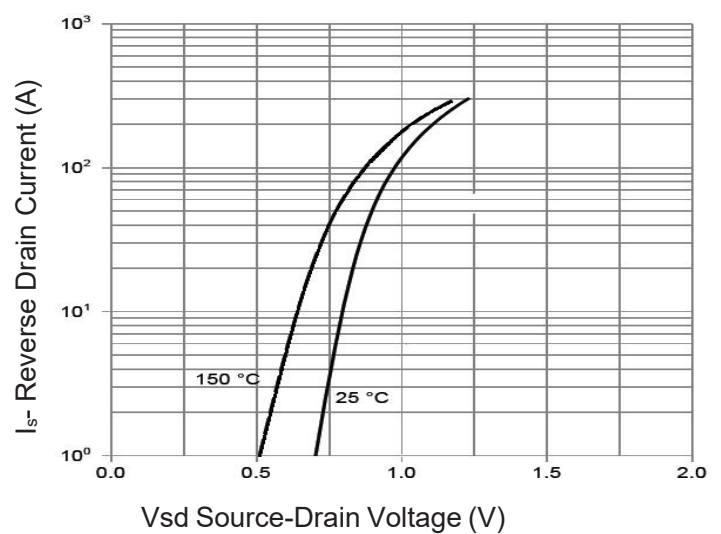
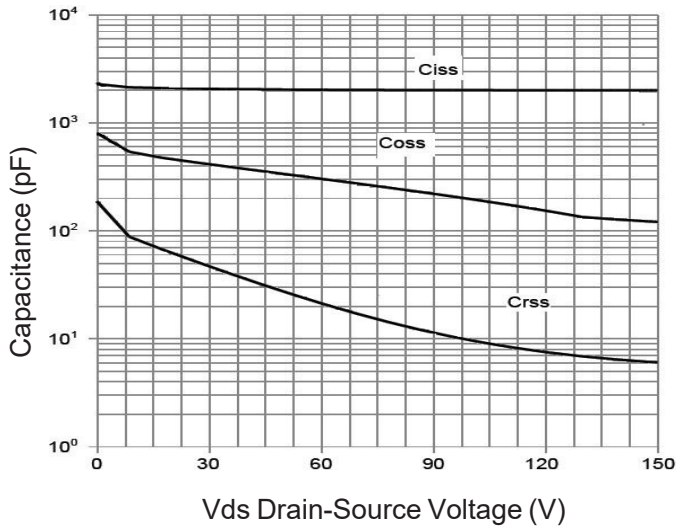
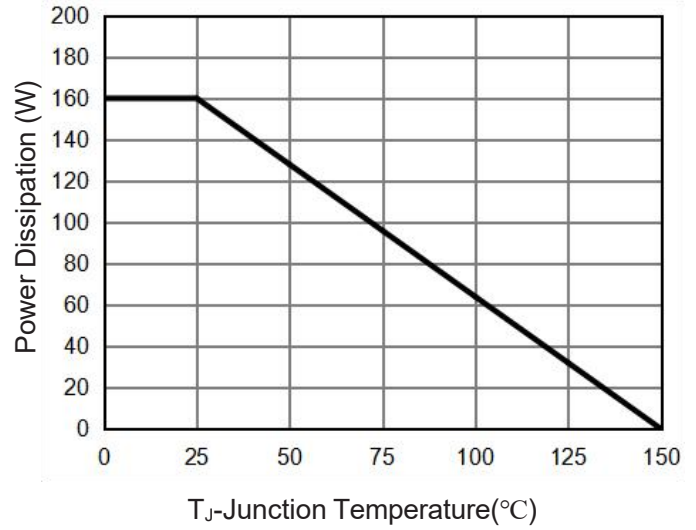
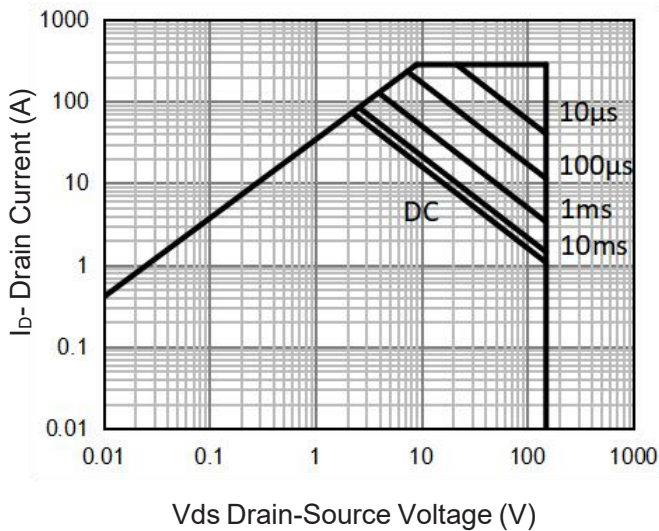
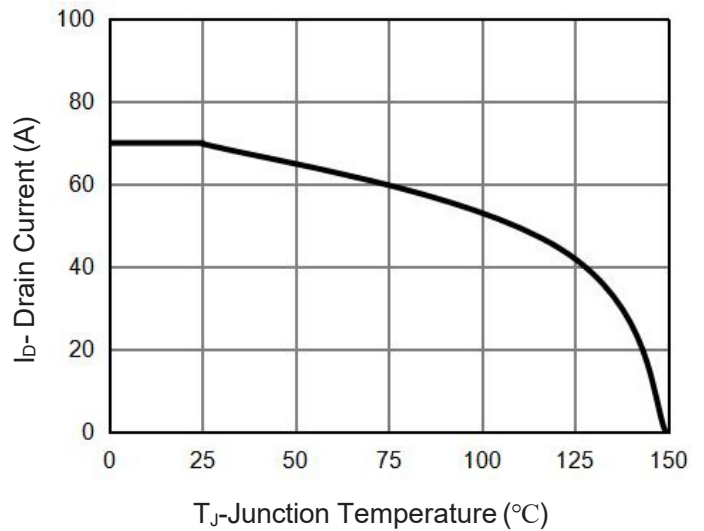
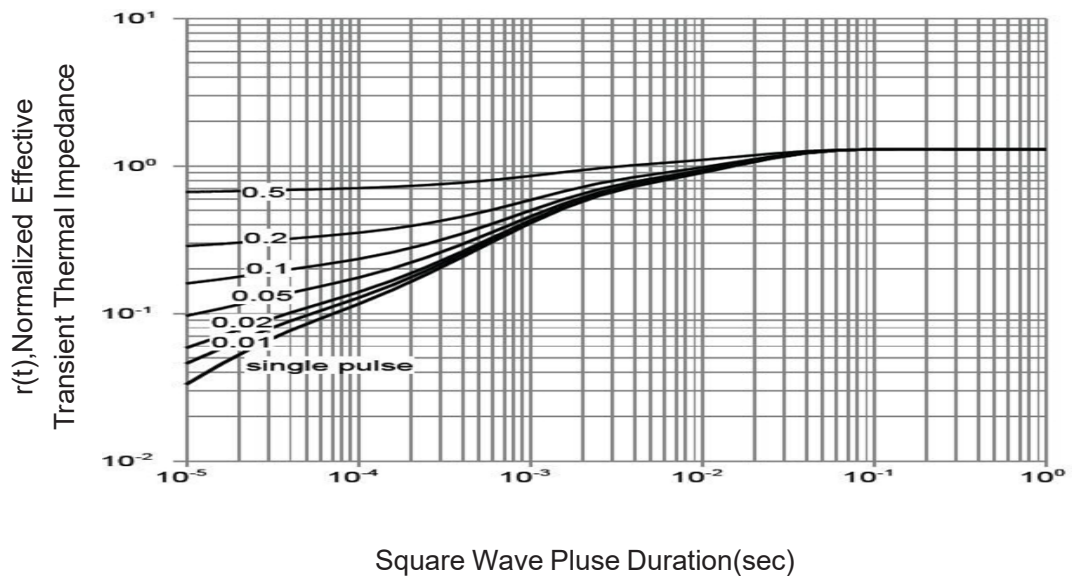


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area (Note 3)

Figure 10 Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance